

# Phase Control Thyristors (Hockey PUK Version), 1650 A



K-P	IIK	(Δ	-24

PRIMARY CHARACTERISTICS					
I <sub>T(AV)</sub>	1650 A				
V <sub>DRM</sub> /V <sub>RRM</sub>	1200 V, 1400 V, 1600 V, 1800 V, 2000 V				
V <sub>TM</sub>	1.73 V				
I <sub>GT</sub>	100 mA				
T <sub>J</sub>	-40 °C to +125 °C				
Package	K-PUK (A-24)				
Circuit configuration	Single SCR				

### **FEATURES**

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case K-PUK (A-24)
- High profile hockey PUK
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

## **TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
		1650	A			
I <sub>T(AV)</sub>	T <sub>hs</sub>	55	°C			
1		3080	A			
I <sub>T</sub> (RMS)	T <sub>hs</sub>	25	°C			
I <sub>TSM</sub>	50 Hz	30 500	^			
	60 Hz	32 000	A			
l <sup>2</sup> t	50 Hz	4651	kA <sup>2</sup> s			
1-1	60 Hz	4250	KA-S			
V <sub>DRM</sub> /V <sub>RRM</sub>		1200 to 2000	V			
tq	Typical	200	μs			
T <sub>J</sub>		-40 to +125	°C			

### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS									
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ MAXIMUM AT T <sub>J</sub> = T <sub>J</sub> MAXIMUM mA					
	12	1200	1300						
	14	1400	1500						
VS-ST1200CK	16	1600	1700	100					
	18	1800	1900						
	20	2000	2100						



ABSOLUTE MAXIMUM RATINGS	S					
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current	1	180° condu	ction, half sine	wave	1650 (700)	Α
at heatsink temperature	I <sub>T(AV)</sub>	double side	(single side) co	oled	55 (85)	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink temp	erature double side cooled	3080	
		t = 10 ms	No voltage		30 500	
Maximum peak, one-cycle	I	t = 8.3  ms	reapplied		32 000	A kA <sup>2</sup> s
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>	Sinusoidal half wave, initial $T_J = T_J$ maximum	25 700	
		t = 8.3 ms	reapplied		26 900	
Maximum 12+ fau fusing		t = 10 ms	No voltage reapplied		4651	
	I <sup>2</sup> t	t = 8.3 ms			4250	
Maximum I <sup>2</sup> t for fusing	1-1	t = 10 ms	100 % V <sub>RRM</sub>		3300	
		t = 8.3  ms	reapplied		3000	
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 ms t	o 10 ms, no vol	tage reapplied	46 510	kA²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$ , $T_J = T_J$ maximum	0.91	V
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			\ \ \
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum			0.21	mΩ
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.19	11122
Maximum on-state voltage	$V_{TM}$	$I_{pk} = 4000 A$	$A, T_J = T_J \text{ maxim}$	num, t <sub>p</sub> = 10 ms sine pulse	1.73	V
Maximum holding current	I <sub>H</sub>	T 25 °C	anodo supely 1	2 V resistive lead	600	mA
Typical latching current	IL	T <sub>J</sub> = 25 °C, anode supply 12 V resistive load		1000	IIIA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega$ , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/µs
Typical delay time	t <sub>d</sub>	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.9	
Typical turn-off time	t <sub>q</sub>	$I_{TM}$ = 550 A, $T_J$ = $T_J$ maximum, dl/dt = 40 A/μs, $V_R$ = 50 V, dV/dt = 20 V/μs, gate 0 V 100 $\Omega$ , $t_p$ = 500 μs	200	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = T <sub>J</sub> maximum linear to 80 % rated V <sub>DRM</sub>	500	V/µs
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	100	mA



TRIGGERING							
PARAMETER	SYMBOL		TEGT COMPITIONS		VALUES		
PARAMETER	STIVIBUL	"=	ST CONDITIONS	TYP.	MAX.	UNITS	
Maximum peak gate power	$P_{GM}$	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	1	6	W	
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	;	3	VV	
Maximum peak positive gate current	I <sub>GM</sub>		$T_J = T_J$ maximum, $t_p \le 5$ ms			Α	
Maximum peak positive gate voltage	+ V <sub>GM</sub>	$T_J = T_J$ maximum,				\ \	
Maximum peak negative gate voltage	- V <sub>GM</sub>		5.0		]		
	I <sub>GT</sub>	T <sub>J</sub> = -40 °C	Maximum required gate trigger/current/voltage are the lowest	200	-	mA	
DC gate current required to trigger		T <sub>J</sub> = 25 °C		100	200		
		T <sub>J</sub> = 125 °C		50	-		
		T <sub>J</sub> = -40 °C	value which will trigger all units	1.4	-		
DC gate voltage required to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C	12 V anode to cathode applied	1.1	3.0	V	
		T <sub>J</sub> = 125 °C		0.9	-		
DC gate current not to trigger	I <sub>GD</sub>		Maximum gate current/voltage	1	0	mA	
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J \text{ maximum}$	not to trigger is the maximum value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.	25	V	

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum operating junction temperature range	TJ	TJ		°C			
Maximum storage temperature range	T <sub>Stg</sub>		-40 to 150				
Maximum thermal resistance,	В	DC operation single side cooled	0.0.42				
junction to heatsink	R <sub>thJ-hs</sub>	DC operation double side cooled	0.021	K/W			
Maximum thermal resistance,	_ n	DC operation single side cooled	0.006	<b>1</b> √ <b>V</b> V			
case to heatsink	R <sub>thC-hs</sub>	DC operation double side cooled	0.003				
Mounting force, ± 10 %			24 500 (2500)	N (kg)			
Approximate weight			425	g			
Case style		See dimensions - link at the end of datasheet K-PUK (A-24)		(A-24)			

△R <sub>thJC</sub> CONDUCTION										
CONDUCTION ANGLE	SINUSOIDAL	CONDUCTION RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS					
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	1E31 CONDITIONS	UNITS				
180°	0.003	0.003	0.002	0.002						
120°	0.004	0.004	0.004	0.004						
90°	0.005	0.005	0.005	0.005	$T_J = T_J$ maximum	K/W				
60°	0.007	0.007	0.007	0.007						
30°	0.012	0.012	0.012	0.012						

### Note

• The table above shows the increment of thermal resistance RthJC when devices operate at different conduction angles than DC

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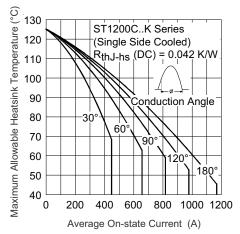


Fig. 1 - Current Ratings Characteristics

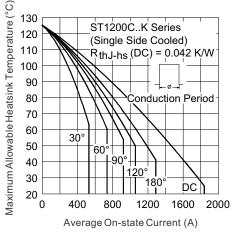


Fig. 2 - Current Ratings Characteristics

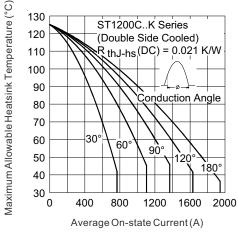


Fig. 3 - Current Ratings Characteristics

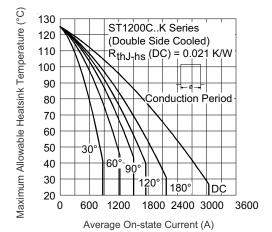


Fig. 4 - Current Ratings Characteristics

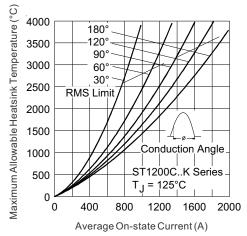


Fig. 5 - On-State Power Loss Characteristics

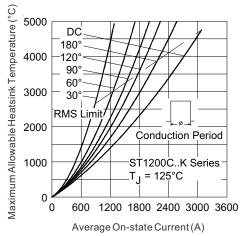
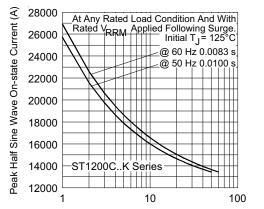


Fig. 6 - On-State Power Loss Characteristics

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Number Of Equal Amplitude Half Cycle Current Pulses (N)

Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

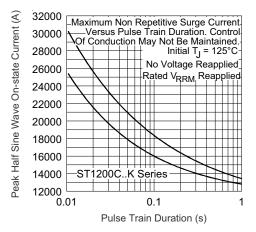


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

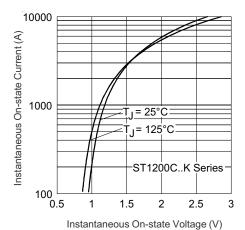


Fig. 9 - On-State Voltage Drop Characteristics

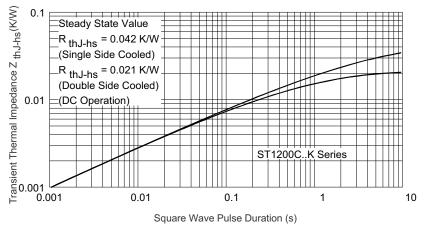


Fig. 10 - Thermal Impedance Z<sub>thJ-hs</sub> Characteristics

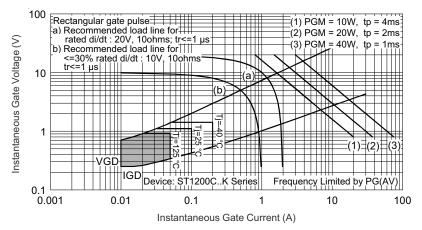
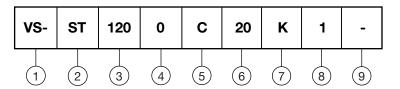


Fig. 11 - Gate Characteristics

### **ORDERING INFORMATION TABLE**

#### **Device code**



1 - Vishay Semiconductors product

2 - Thyristor

3 - Essential part number

- 0 = converter grade

5 - C = ceramic PUK

6 - Voltage code: code x 100 = V<sub>RRM</sub> (see Voltage Ratings table)

7 - K = PUK case K-PUK (A-24)

8 - 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)

9 - Critical dV/dt: • None = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

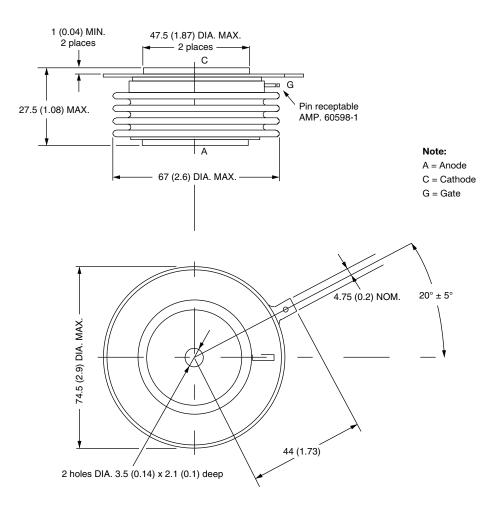
LINKS TO RELAT	TED DOCUMENTS
Dimensions	www.vishay.com/doc?95081



# K-PUK (A-24)

## **DIMENSIONS** in millimeters (inches)

Creepage distance: 28.88 (1.137) minimum Strike distance: 17.99 (0.708) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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